

Supporting information

Pressure-assisted annealing method for high quality CsPbBr₃ film deposited by sequential thermal evaporation

Jingchen Hua^a, Xi Deng^a, Cheng Niu^a, Fuzhi Huang^a, Yong Peng^a, Wangnan Li^{*b}, Zhiliang Ku^{*a,b}, and Yibing Cheng^{a,c}

^a State Key Laboratory of Advanced Technologies for Materials Synthesis and Processing, International School of Materials Science and Engineering, Wuhan University of Technology, 122 Luoshui Road, Wuhan, Hubei, P. R. China. Email: zhiliang.ku@whut.edu.cn

^b Hubei Key Laboratory of Low Dimensional Optoelectronic Material and Devices, Hubei University of Arts and Science, 296 Longzhong Road, Xiangyang, Hubei Province, P. R. China

^c Department of Materials Science and Engineering, Monash University, Wellington Road, Clayton, VIC3800, Australia

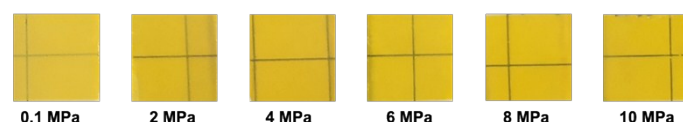


Figure S1. Photograph of CsPbBr₃ films with different annealing pressures.

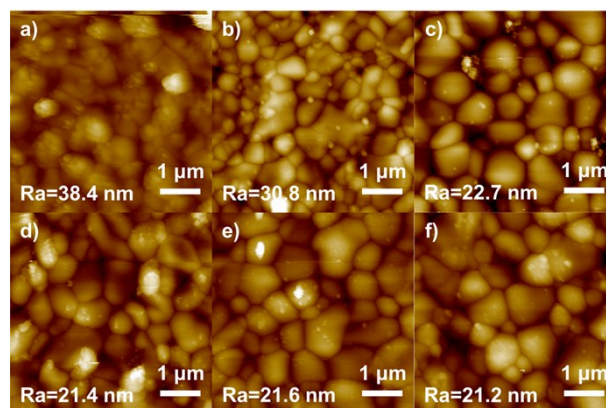


Figure S2. AFM images of CsPbBr₃ films with the different annealing pressures of a) 0.1 MPa, b) 2 MPa, c) 4 MPa, d) 6 MPa, e) 8 MPa, f) 10 MPa.

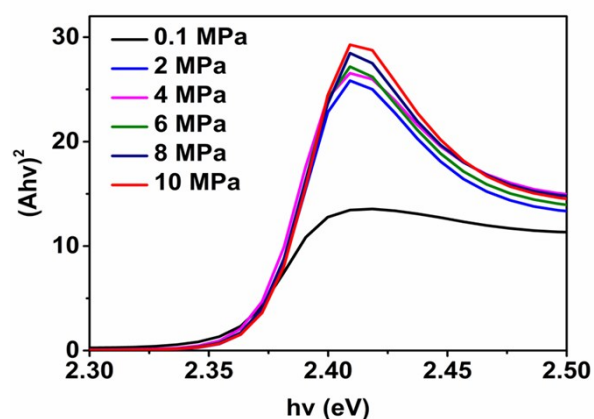


Figure S3. Tauc plots: $(Ah\nu)^2$ vs $h\nu$ curves of the CsPbBr₃ films prepared with different annealing

pressures.

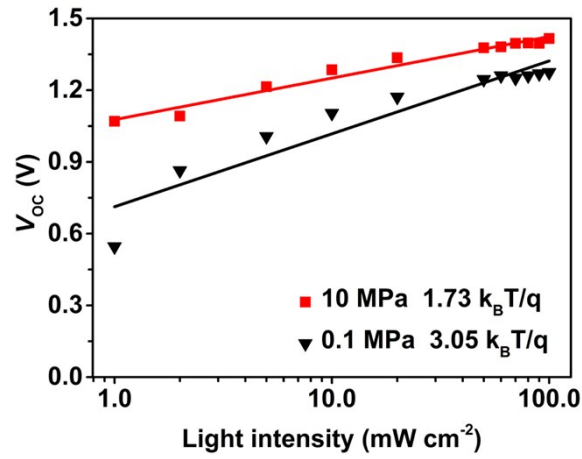


Figure S4. V_{oc} versus various light intensities (from 100 mW cm^{-2} to 1 mW cm^{-2}) plots of AP-0.1 and AP-0.1 devices.

Table S1. The peak intensity parameters extracted from XRD patterns in Figure 3.

Sample	$\text{FTO}_{(110)}$	$\text{CsPbBr}_3(200)$	$\text{CsPbBr}_3/\text{FTO}_{(200)}$
0.1 MPa	618	649	1.05
2 MPa	757	873	1.15
4 MPa	725	947	1.30
6 MPa	732	1175	1.61
8 MPa	684	1528	2.20
10 MPa	653	1413	2.16

Table S2. The parameters extracted from the time-resolved PL spectra based on the PA-0.1 and PA-10 samples.

Sample	τ_{avg} [ns]	τ_1 [ns]	τ_2 [ns]	A_1 [%]	A_2 [%]
PA-0.1 with ETL	3.35	0.19	3.88	86	25
PA-10 with ETL	8.99	1.11	9.60	38	56
PA-0.1 without ETL	2.64	0.28	3.05	71	38
PA-10 without ETL	1.35	0.12	1.61	88	32

Table S3. The statistical photovoltaic parameters of the 6 batches of devices.

Device	Scan direction	J_{sc} [mA cm ⁻²]	V_{oc} [V]	FF	PCE [%]	Maximum PCE [%]
0.1 MPa	reverse	3.006	1.243	0.546	2.148	2.79
	forward	2.997	1.241	0.462	1.817	2.53
2 MPa	reverse	5.218	1.292	0.637	4.162	4.55
	forward	5.202	1.291	0.502	3.280	3.62
4 MPa	reverse	5.806	1.318	0.706	5.084	5.54
	forward	5.793	1.311	0.621	4.472	5.03
6 MPa	reverse	5.984	1.374	0.737	5.915	6.35
	forward	5.977	1.371	0.654	5.25	5.78
8 MPa	reverse	6.444	1.398	0.748	6.73	7.21
	forward	6.436	1.390	0.661	5.95	6.48
10 MPa	reverse	6.459	1.400	0.746	6.74	7.22
	forward	6.451	1.394	0.675	6.10	6.53